Number	
1	щ р
	29
3 0 ((kozo nearz nakamura or toshiaki near2 saishoji or hirotaka nearz nakajima or masashi near2 shishimura or toshirou nearz shimanuki).in.) and heat near2 treat\$5 and ramp\$5 near2 rate	29
- 20 "5954873" USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	29
- 17 "5968264" - 16 "5788763" - 16 "5788763" - 17 "5968264" - 18 "5788763" - 19 "5788763" - 19 "5788763" - 10 "5788763" - 11 "5788763" - 12 "5788763" - 13 "5788763" - 14 "5788763" - 15 "5788763" - 16 "5788763" - 17 "5788763" - 17 "5788763" - 17 "5788763" - 18 "5788763"	17
- 16 "5788763" IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PG	17
373 czochralski and (temperature adj gradient) and (speed or velocity) USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	17
- 332 czochralski and (temperature adj gradient) same (speed or velocity or rate) - 606 memc.as. - 606 memc.as. - 174 memc.as. and czochralski - 53 memc.as. and czochralski and gradient - 55 memc.as. and czochralski and gradient - 56 memc.as. and czochralski and gradient - 57 memc.as. and czochralski and gradient - 58 memc.as. and czochralski and gradient - 59 memc.as. and czochralski and gradient - 50 memc.as. and czochralski and gradient	۱7
- 174 memc.as. and czochralski uspat; Uspat; Uspat; Uspat; Uspat; Uspat; Uspat; Ism_TDB uspat; Uspat	١ 7
The memotion of the memotion o	.7
53 memc.as. and czochralski and gradient USPAT; 2003/05/04	.7
EPO; JPO; DERWENT;	14
- 873 wafer and (anneal\$3 or (heat adj treat\$4) USPAT; US-PGPUB; 16:27 PTP) and czochralski PTP or DERWENT;	.7
- 598 wafer and (anneal\$3 or (heat adj treat\$4) uspat; cr (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski EPO; JPO; DERWENT; IBM TDB	7

-	256	,,,,,, ,, ,	USPAT;	2003/12/30
		(si or silicon) near2 (wafer or	US-PGPUB;	15:42
		substrate) same temperature near10 ("700"	EPO; JPO;	
		or "800" or "650" or "750" or "900" or	DERWENT;	
		"950")	IBM_TDB	
-	38	(====================================	USPAT;	2003/12/30
	1	(si or silicon) near2 (wafer or	US-PGPUB;	15:47
İ		substrate) same temperature near10 ("700"	EPO; JPO;	
		or "800" or "650" or "750" or "900" or	DERWENT;	•
		"950") same rate	IBM_TDB	
-	15	,,,,, ,	USPAT;	2003/12/30
Ì		(si or silicon) near2 (wafer or	US-PGPUB;	15:47
		substrate) same temperature same rate	EPO; JPO;	
		near2 less	DERWENT;	
1		1	IBM_TDB	<u>.</u>
-	248	1	USPAT;	2004/01/05
		near5 (speed or rate) and czochralski	US-PGPUB;	10:04
			EPO; JPO;	
		·	DERWENT;	
	-	55 67200	IBM_TDB	
-	2	5567399.pn.	USPAT;	2004/01/05
			US-PGPUB;	10:32
			EPO; JPO;	
			DERWENT;	
	1 254	/Ai	IBM_TDB	0004/55/55
-	251	,	USPAT;	2004/01/05
	1	near5 (speed or rate) and czochralski	US-PGPUB;	10:34
			EPO; JPO;	
			DERWENT;	
	1 4 5		IBM_TDB	
<u> </u>	145		USPAT;	2004/01/05
		near5 pull\$3 near3 (speed or rate) and	US-PGPUB;	11:08
		czochralski	EPO; JPO;	
	1		DERWENT;	
		0215000	IBM_TDB	
-	1	9315882.pn.	USPAT;	2004/01/05
			US-PGPUB;	11:08
		*	EPO; JPO;	
			DERWENT;	
_	2	00315002 mm	IBM_TDB	2004/01/05
-	4	09315882.pn.	USPAT;	2004/01/05
			US-PGPUB;	11:08
1			EPO; JPO;	
F			DERWENT;	
_	5663	heat near? treated same (si am sili heat	IBM_TDB	2004/07/10
	7003	heat near2 treat\$4 same (si or silicon) near5 (single near2 crystal\$5 or wafer)	USPAT;	2004/07/19
		nears (single near2 Crystalss or water)	US-PGPUB;	17:05
			EPO; JPO;	
			DERWENT;	
_	1655	heat near2 treat\$4 near10 temperature	<pre>IBM_TDB USPAT;</pre>	2004/07/19
	1033	same (si or silicon) near5 (single near2	USPAT; US-PGPUB;	17:05
		crystal\$5 or wafer)	EPO; JPO;	17:05
		OTINGATAS OF MOTET!	DERWENT;	
			IBM TDB	
_	113	heat near2 treat\$4 near10 temperature	USPAT;	2004/07/19
	113	near10 (ramp\$4 or rate) same (si or	US-PGPUB;	17:43
		silicon) near5 (single near2 crystal\$5 or	EPO; JPO;	11.13
		wafer)	DERWENT;	
		"ALGE!	IBM TDB	
_	2	"07165495"	USPAT;	2004/07/19
			US-PGPUB;	17:14
			EPO; JPO;	7/.13
	1		DERWENT;	
]	i	IBM TDB	
_	182	heat near2 treat\$4 near10 temperature	USPAT;	2004/07/19
	102	near nearz treat; nearlo temperature near5 low same (si or silicon) near5	US-PGPUB;	17:49
		(single near2 crystal\$5 or wafer)	EPO; JPO;	11.43
	1	(DERWENT;	
	1. 1.	-	IBM TDB	
	1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1		TULL TUD	,

<u> </u>	15	heat nearly tweeted nearly termenature	THERRE	10004/05/00
	13	1	USPAT;	2004/07/20
		near5 initial\$5 same (si or silicon)	US-PGPUB;	09:08
		near5 (single near2 crystal\$5 or wafer)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
-	17	heat near2 treat\$4 near10 temperature	USPAT;	2004/07/20
		near5 start\$5 same (si or silicon) near5	US-PGPUB;	09:23
		(single near2 crystal\$5 or wafer)	EPO; JPO;	
		<u>-</u> , ,	DERWENT;	
			IBM TDB	
-	195	(sueoka near2 koji or koike near2 yasuo	USPAT;	2004/07/20
		or sadamitsu near2 shinsuke).in.	US-PGPUB;	09:24
			EPO; JPO;	03.24
			DERWENT;	
			IBM TDB	
_	2	((sueoka near2 koji or koike near2 yasuo	USPAT;	2004/07/20
	_	or sadamitsu near2 shinsuke).in.) and	l ·	2004/07/20
		(start\$5 or initial\$5 or starting	US-PGPUB;	09:25
İ	İ		EPO; JPO;	
		initiat\$5) near6 temperature	DERWENT;	
	26	(/	IBM_TDB	
_	26	((sueoka near2 koji or koike near2 yasuo	USPAT;	2004/07/29
		or sadamitsu near2 shinsuke).in.) and	US-PGPUB;	11:23
		temperature same (heat near2 treat\$5 or	EPO; JPO;	
		anneal\$5) same (si or silicon) near5	DERWENT;	
		(substrate or wafer)	IBM TDB	